



ON Semiconductor®

ISL9V5045S3ST-F085

EcoSPARK® N-Channel Ignition IGBT

500mJ, 450V

Features

- SCIS Energy = 500mJ at $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive
- Qualified to AEC Q101
- RoHS Compliant

Applications

- Automotive Ignition Coil Driver Circuits
- Coil - On Plug Applications

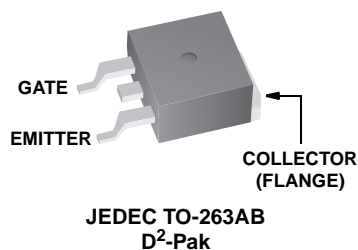
General Description

The ISL9V5045S3ST-F085 is next generation ignition IGBT that offer outstanding SCIS capability in the industry standard D2-Pak (TO-263) plastic package. This device is intended for use in automotive ignition circuits, specifically as a coil drivers. Internal diodes provide voltage clamping without the need for external components.

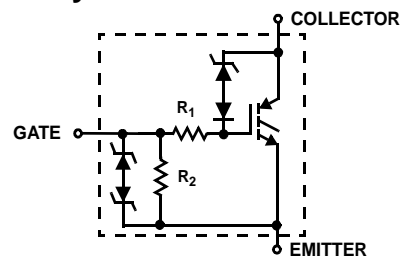


ISL9V5045S3ST-F085 N-Channel Ignition IGBT

Package



Symbol



Device Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
BV_{CER}	Collector to Emitter Breakdown Voltage ($I_C = 1\text{ mA}$)	480	V
BV_{ECS}	Emitter to Collector Voltage - Reverse Battery Condition ($I_C = 10\text{ mA}$)	24	V
E_{SCIS25}	At Starting $T_J = 25^\circ\text{C}$, $I_{SCIS} = 39.2\text{ A}$, $L = 650\ \mu\text{H}$	500	mJ
$E_{SCIS150}$	At Starting $T_J = 150^\circ\text{C}$, $I_{SCIS} = 31.1\text{ A}$, $L = 650\ \mu\text{H}$	315	mJ
I_{C25}	Collector Current Continuous, At $T_C = 25^\circ\text{C}$, See Fig 9	51	A
I_{C110}	Collector Current Continuous, At $T_C = 110^\circ\text{C}$, See Fig 9	43	A
V_{GEM}	Gate to Emitter Voltage Continuous	± 10	V
P_D	Power Dissipation Total $T_C = 25^\circ\text{C}$	300	W
	Power Dissipation Derating $T_C > 25^\circ\text{C}$	2	W/ $^\circ\text{C}$
T_J	Operating Junction Temperature Range	-40 to 175	$^\circ\text{C}$
T_{STG}	Storage Junction Temperature Range	-40 to 175	$^\circ\text{C}$
T_L	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	$^\circ\text{C}$
T_{pkg}	Max Lead Temp for Soldering (Package Body for 10s)	260	$^\circ\text{C}$
ESD	Electrostatic Discharge Voltage at 100pF, 1500 Ω	4	kV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
V5045S	ISL9V5045S3ST-F085	TO-263AB	330mm	24mm	800

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off State Characteristics

BV_{CER}	Collector to Emitter Breakdown Voltage	$I_C = 2\text{ mA}$, $V_{GE} = 0$, $R_G = 1\text{ K}\Omega$, See Fig. 15 $T_J = -40\text{ to }150^\circ\text{C}$	420	450	480	V	
BV_{CES}	Collector to Emitter Breakdown Voltage	$I_C = 10\text{ mA}$, $V_{GE} = 0$, $R_G = 0$, See Fig. 15 $T_J = -40\text{ to }150^\circ\text{C}$	445	475	505	V	
BV_{ECS}	Emitter to Collector Breakdown Voltage	$I_C = -75\text{ mA}$, $V_{GE} = 0\text{ V}$, $T_C = 25^\circ\text{C}$	30	-	-	V	
BV_{GES}	Gate to Emitter Breakdown Voltage	$I_{GES} = \pm 2\text{ mA}$	± 12	± 14	-	V	
I_{CER}	Collector to Emitter Leakage Current	$V_{CER} = 320\text{ V}$, $R_G = 1\text{ K}\Omega$, See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	25	μA
			$T_C = 150^\circ\text{C}$	-	-	1	mA
I_{ECS}	Emitter to Collector Leakage Current	$V_{EC} = 24\text{ V}$, See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	1	mA
			$T_C = 150^\circ\text{C}$	-	-	40	mA
R_1	Series Gate Resistance		-	100	-	Ω	
R_2	Gate to Emitter Resistance		10K	-	30K	Ω	

On State Characteristics

$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 10\text{ A}$, $V_{GE} = 4.0\text{ V}$	$T_C = 25^\circ\text{C}$, See Fig. 4	-	1.25	1.60	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 15\text{ A}$, $V_{GE} = 4.5\text{ V}$	$T_C = 150^\circ\text{C}$	-	1.47	1.80	V

Dynamic Characteristics

$Q_{G(ON)}$	Gate Charge	$I_C = 10A, V_{CE} = 12V,$ $V_{GE} = 5V, \text{ See Fig. 14}$	-	32	-	nC	
$V_{GE(TH)}$	Gate to Emitter Threshold Voltage	$I_C = 1.0mA,$ $V_{CE} = V_{GE},$ See Fig. 10	$T_C = 25^\circ C$	1.3	-	2.2	V
			$T_C = 150^\circ C$	0.75	-	1.8	V
V_{GEP}	Gate to Emitter Plateau Voltage	$I_C = 10A,$ $V_{CE} = 12V$	-	3.0	-	V	

Switching Characteristics

$t_{d(ON)R}$	Current Turn-On Delay Time-Resistive	$V_{CE} = 14V, R_L = 1\Omega,$ $V_{GE} = 5V, R_G = 1K\Omega$ $T_J = 25^\circ C, \text{ See Fig. 12}$	-	0.7	4	μs
t_{rR}	Current Rise Time-Resistive		-	2.1	7	μs
$t_{d(OFF)L}$	Current Turn-Off Delay Time-Inductive	$V_{CE} = 300V, L = 2mH,$ $V_{GE} = 5V, R_G = 1K\Omega$ $T_J = 25^\circ C, \text{ See Fig. 12}$	-	10.8	15	μs
t_{fL}	Current Fall Time-Inductive		-	2.8	15	μs
SCIS	Self Clamped Inductive Switching	$T_J = 25^\circ C, L = 650 \mu H,$ $R_G = 1K\Omega, V_{GE} = 5V, \text{ See}$ Fig. 1 \& 2	-	-	500	mJ

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction-Case	TO-263	-	-	0.5	$^\circ C/W$
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Typical Characteristics

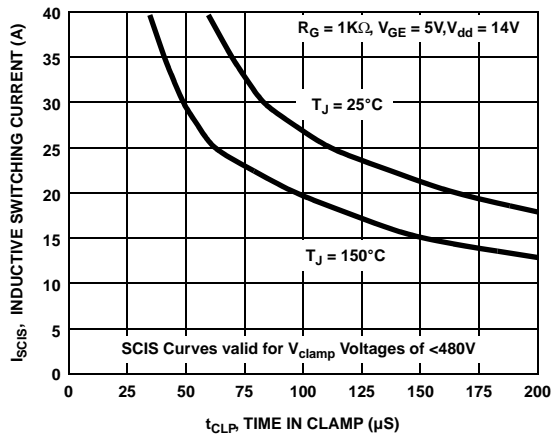


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

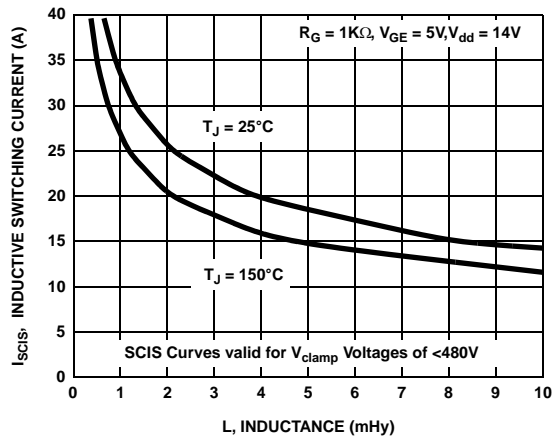


Figure 2. Self Clamped Inductive Switching Current vs Inductance

Typical Characteristics (Continued)

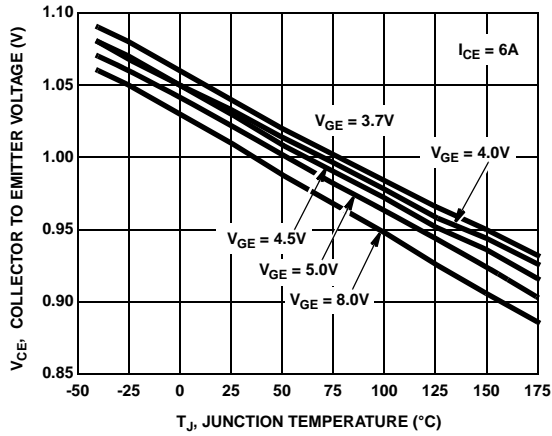


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

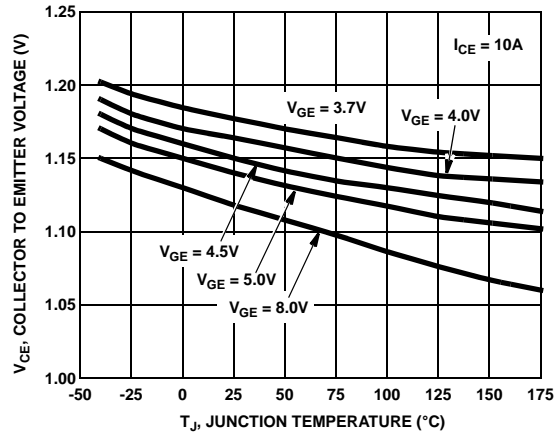


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

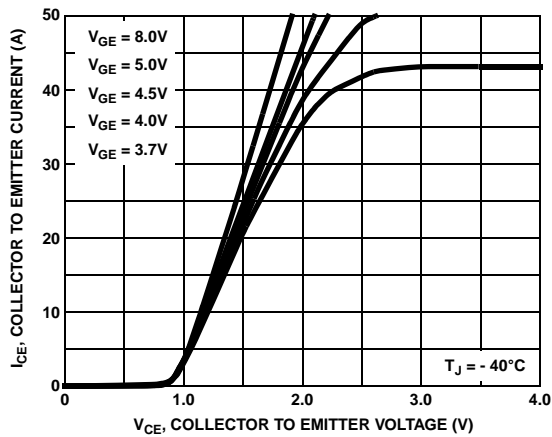


Figure 5. Collector Current vs Collector to Emitter On-State Voltage

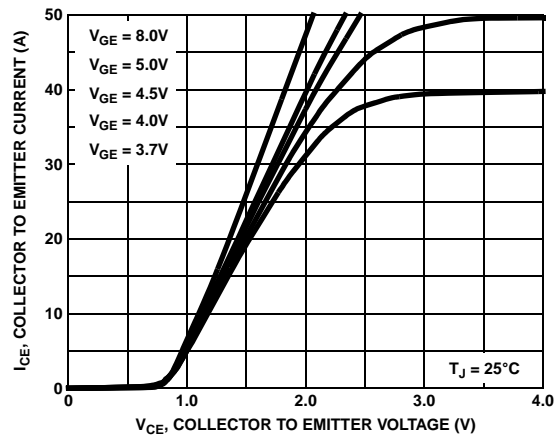


Figure 6. Collector Current vs Collector to Emitter On-State Voltage

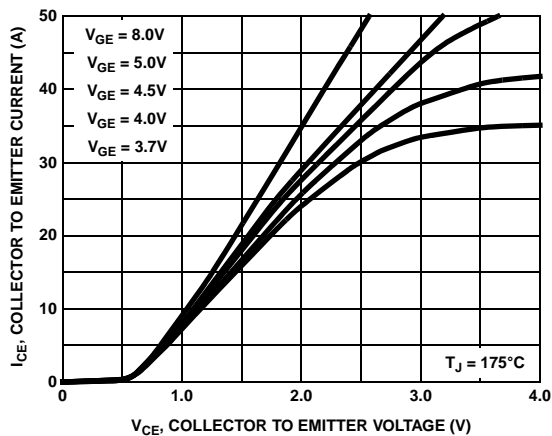


Figure 7. Collector to Emitter On-State Voltage vs Collector Current

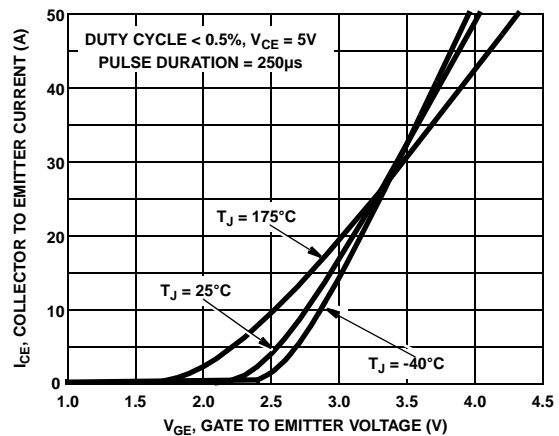


Figure 8. Transfer Characteristics

Typical Characteristics (Continued)

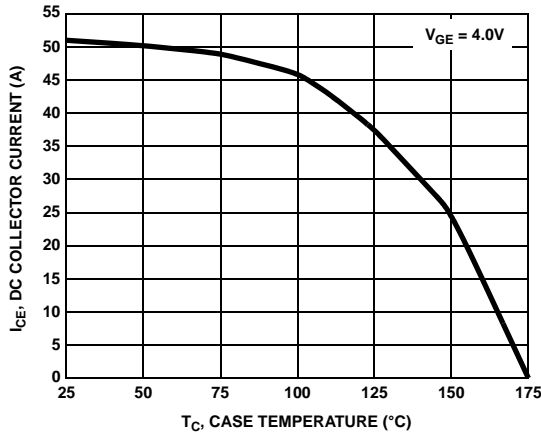


Figure 9. DC Collector Current vs Case Temperature

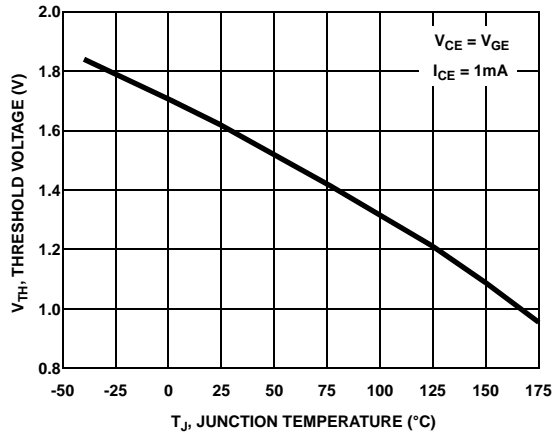


Figure 10. Threshold Voltage vs Junction Temperature

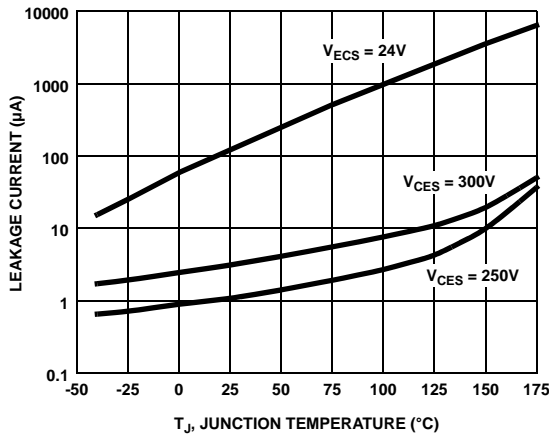


Figure 11. Leakage Current vs Junction Temperature

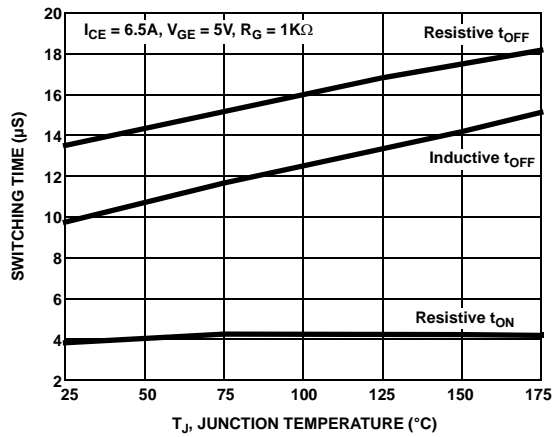


Figure 12. Switching Time vs Junction Temperature

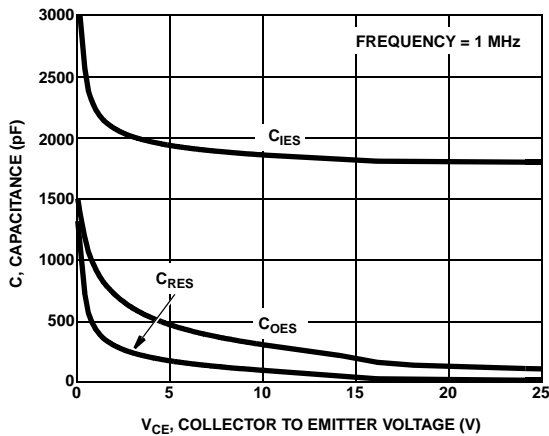


Figure 13. Capacitance vs Collector to Emitter Voltage

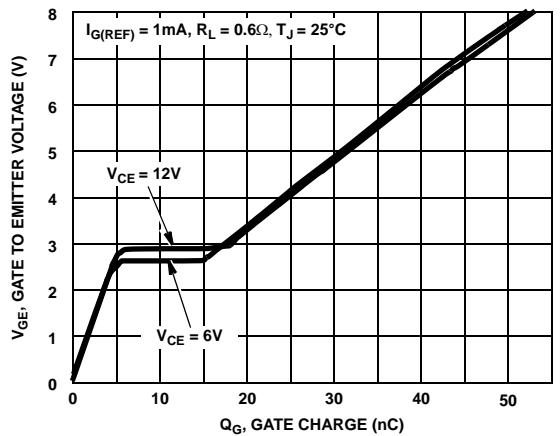


Figure 14. Gate Charge

Typical Characteristics (Continued)

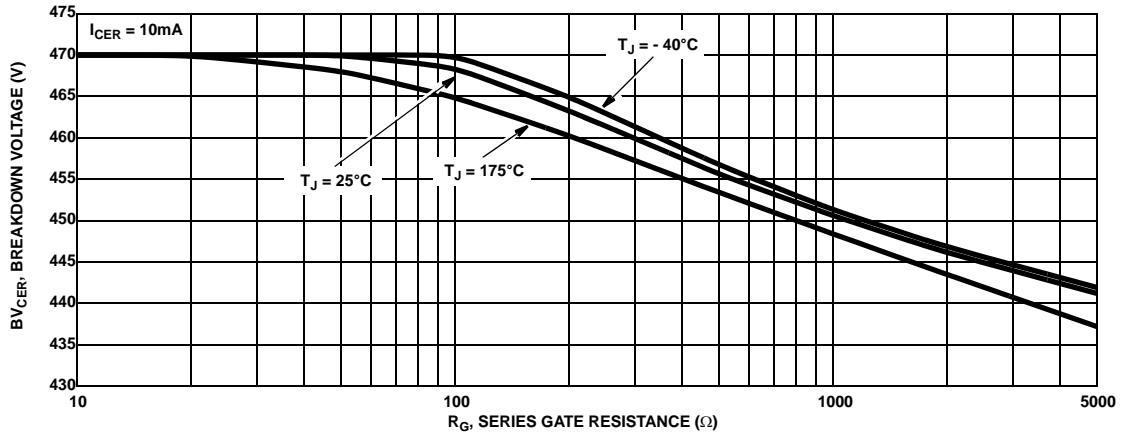


Figure 15. Breakdown Voltage vs Series Gate Resistance

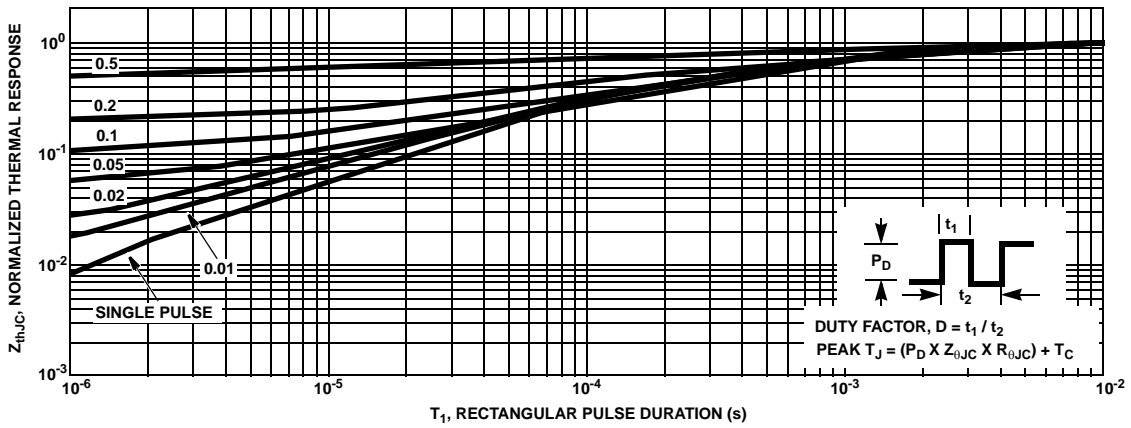


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

Test Circuits and Waveforms

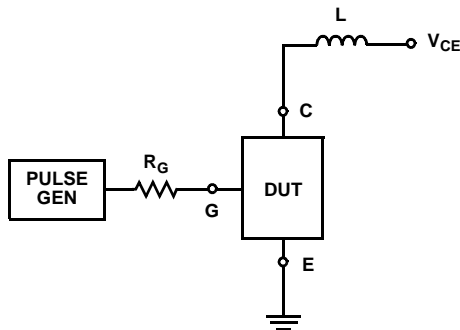


Figure 17. Inductive Switching Test Circuit

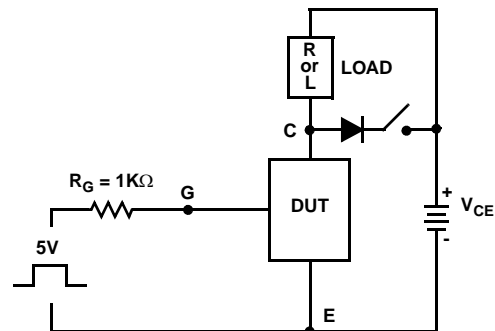


Figure 18. t_{ON} and t_{OFF} Switching Test Circuit

Test Circuits and Waveforms (Continued)

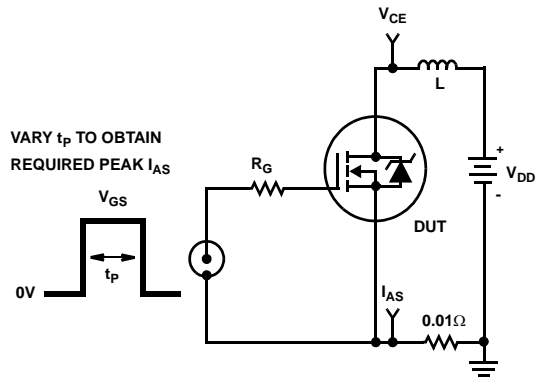


Figure 19. Energy Test Circuit

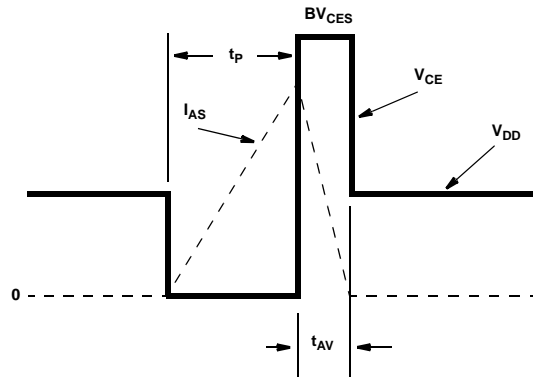


Figure 20. Energy Waveforms

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